N-Channel 200-V (D-S) MOSFET

Key Features:

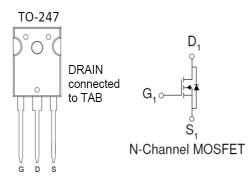
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical	Дþ	plica	atior	ıs:
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Hot Swap Inrush Limit Circuits Uninterruptible Power Supplies and Inverters Motor Speed Controls

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)		
200	40 @ V _{GS} = 10V	100 ^a		





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage	V_{DS}	200	V			
Gate-Source Voltage		V_{GS}	±20	V		
Continuous Drain Current a	T _C =25°C	I _D	100	Α		
Pulsed Drain Current ^b		I _{DM}	400	^		
Continuous Source Current (Diode Conduction) ^a	T _C =25°C	I _S	100	Α		
Power Dissipation ^a	T _C =25°C	P_{D}	500	W		
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient °	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	0.29	C/VV		

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

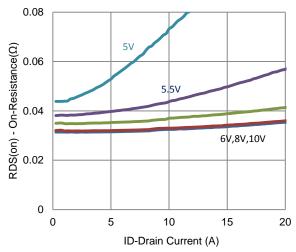
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	125			Α	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			40	mΩ	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		24		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 50 \text{ A}, V_{GS} = 0 \text{ V}$		0.97		V	
	Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V},$		153			
Gate-Source Charge	Q_{gs}	$I_{D} = 20 \text{ A}$		33		nC	
Gate-Drain Charge	Q_gd	10 - 20 77		60			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 100 \text{ V}, R_{I} = 5 \Omega,$		55			
Rise Time	t _r	$I_{DS} = 100 \text{ V}, \text{ RL} = 3.22,$ $I_{D} = 20 \text{ A},$		48		ns	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		189		113	
Fall Time	t _f	V GEN - 10 V, TVGEN 0 12		48			
Input Capacitance	C _{iss}			8242			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		410		pF	
Reverse Transfer Capacitance	C_{rss}			332			

Notes

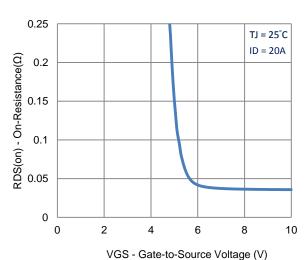
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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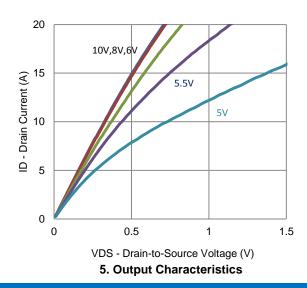
Typical Electrical Characteristics

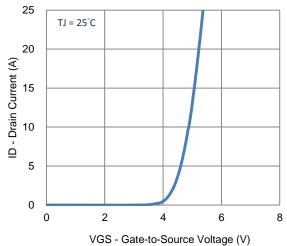


1. On-Resistance vs. Drain Current

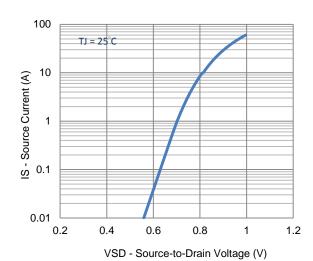


3. On-Resistance vs. Gate-to-Source Voltage

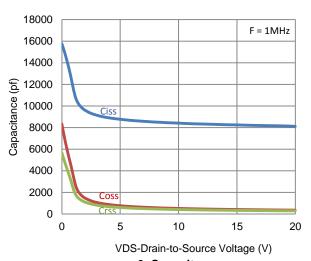




2. Transfer Characteristics

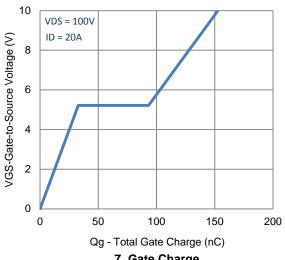


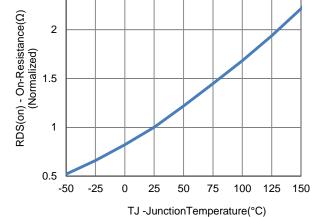
4. Drain-to-Source Forward Voltage



Typical Electrical Characteristics

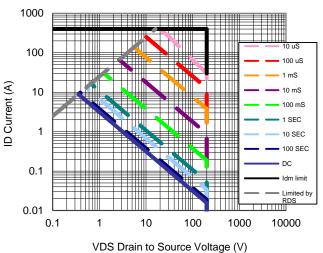
2.5

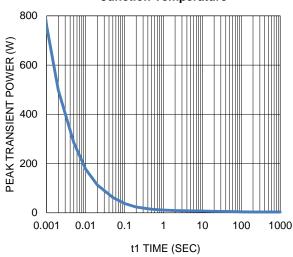




7. Gate Charge

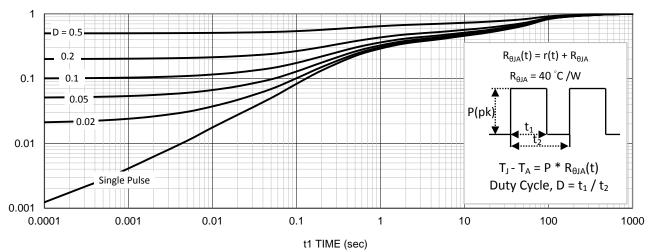






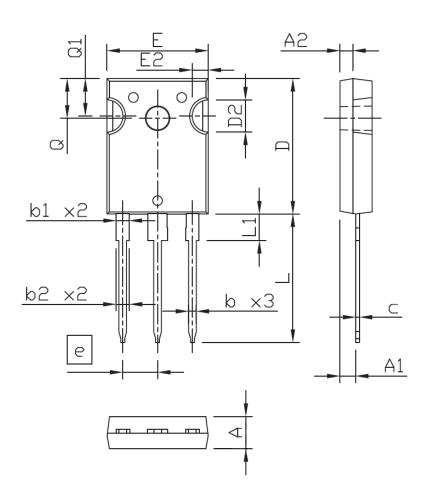
9. Safe Operating Area

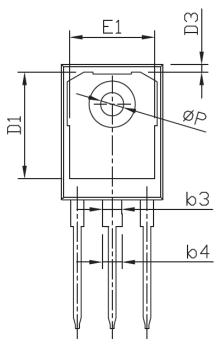
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information





	DIMENSIONS IN MILLIMETERS				
SYMBOLS	MIN	NDM	MAX		
Α	4,90	5,00	5,10		
A1	2.32	2.42	2.52		
A2	1,90	2,00	2,10		
b	1.17	1.22	1.27		
b1	1.97	2.02	2.07		
b2	2.00	2.10	2,20		
b3	2.97	3.02	3.07		
b4	3.00	3.10	3,20		
С	0.59	0.62	0.66		
D	20,90	21,00	21,10		
D1	16.25	16.55	16.85		
<u>D5</u>	5.00 TYP				
D3	1.05	1.20	1.35		
е	5.44 BSC				
Е	15.70	15.80	15.90		
E1	13.06	13.26	13.46		
E2	2.50 TYP				
L	19.72	19.92	20.12		
L1			4,30		
Q	6.15 BSC				
Q1	5,60	5,80	6.00		
ØΡ	3,55	3.60	3.65		